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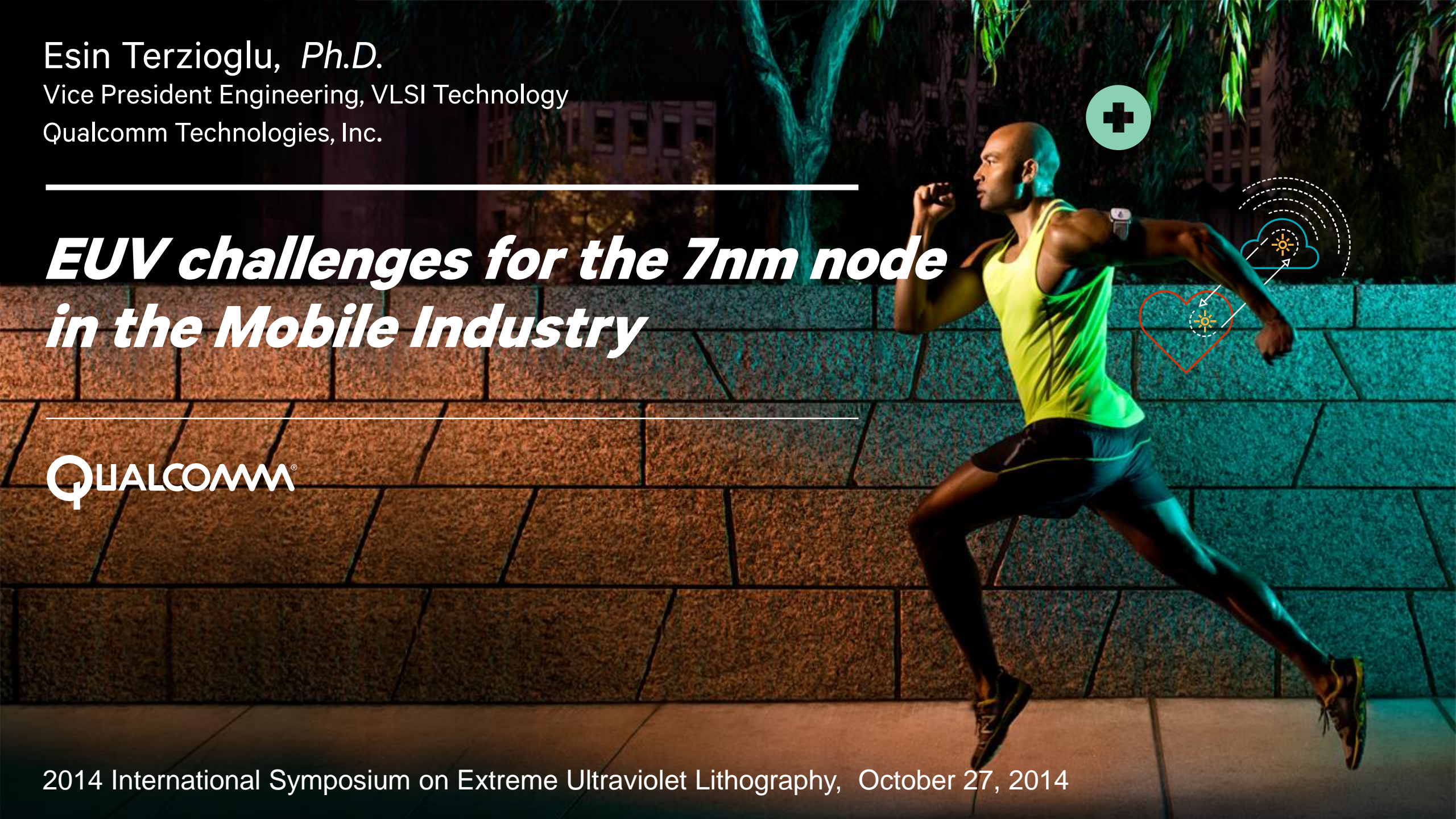
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# ***EUV challenges for the 7nm node in the Mobile Industry***

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2014 International Symposium on Extreme Ultraviolet Lithography, October 27, 2014



# Agenda

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Mobile Revolution !

...and silicon technology requirements

Mobile Silicon Technology Roadmap

CMOS Scaling Cost Challenges

EUV and N7

Summary



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# Mobile Revolution !

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# Continued smartphone momentum

World's most pervasive technology platform

~8B

Cumulative smartphone  
unit shipments forecast  
between 2014-2018



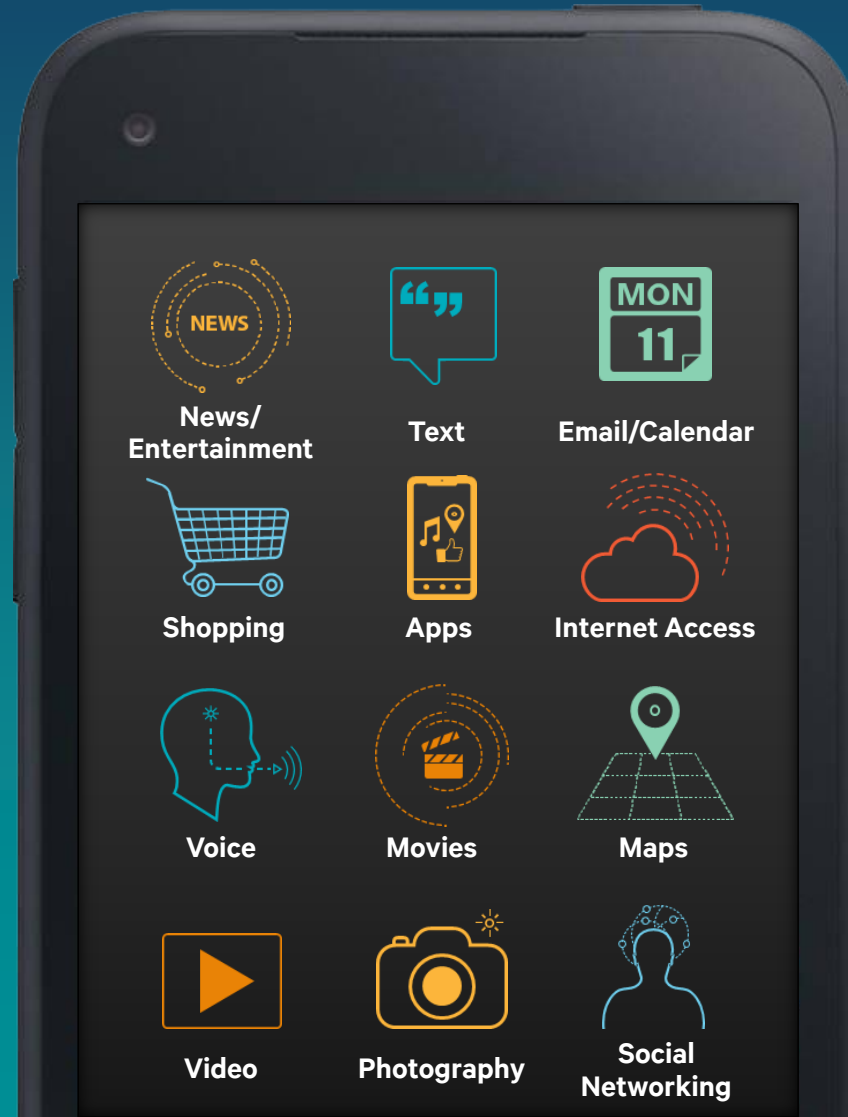
# Smartphone: Our most personal + powerful device

**~106**

Avg. number of daily app launches by US Android users

**~75%**

18-24 year olds reach for it immediately after waking up



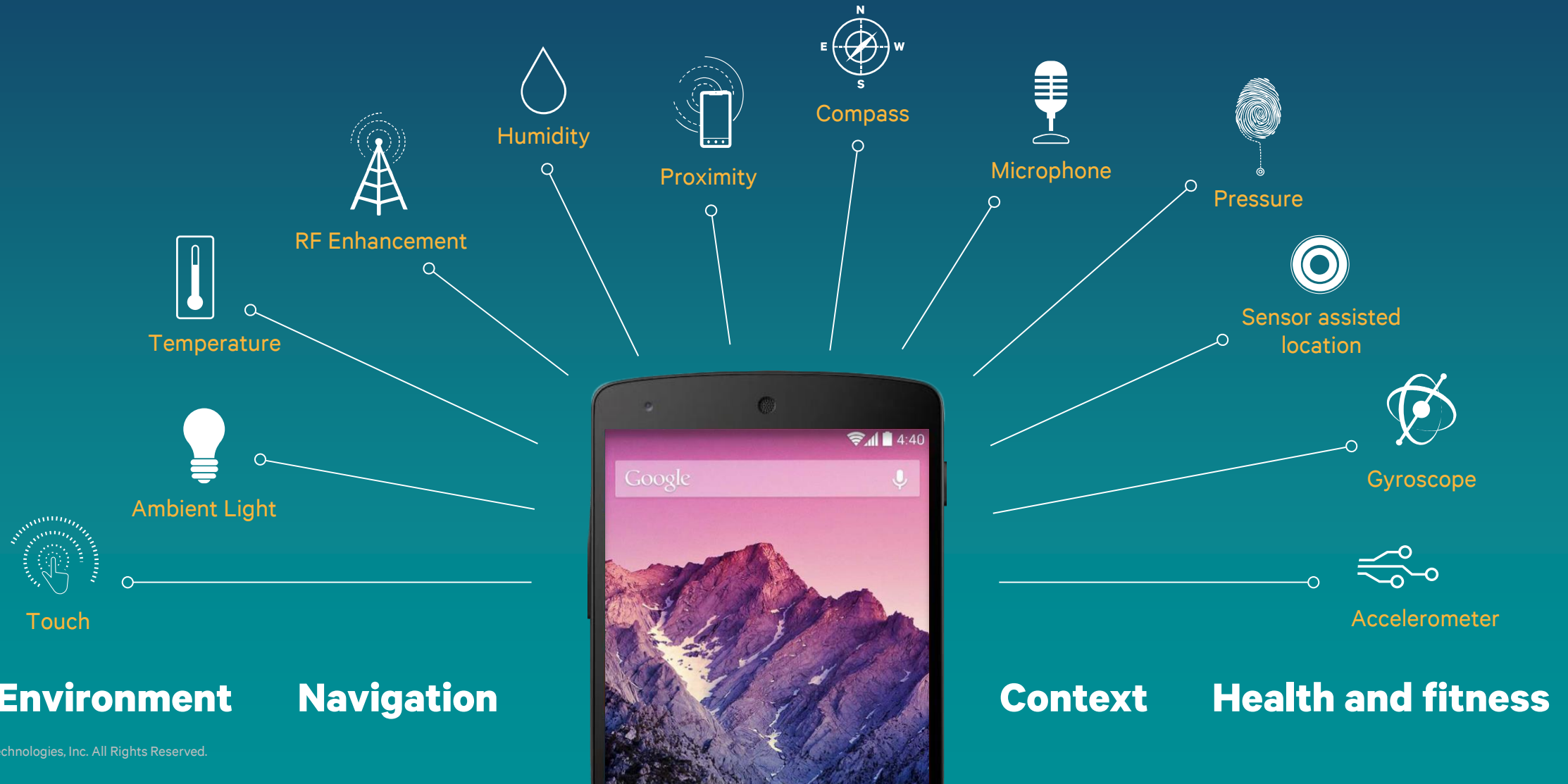
**~94%**

Use their device to look for local information

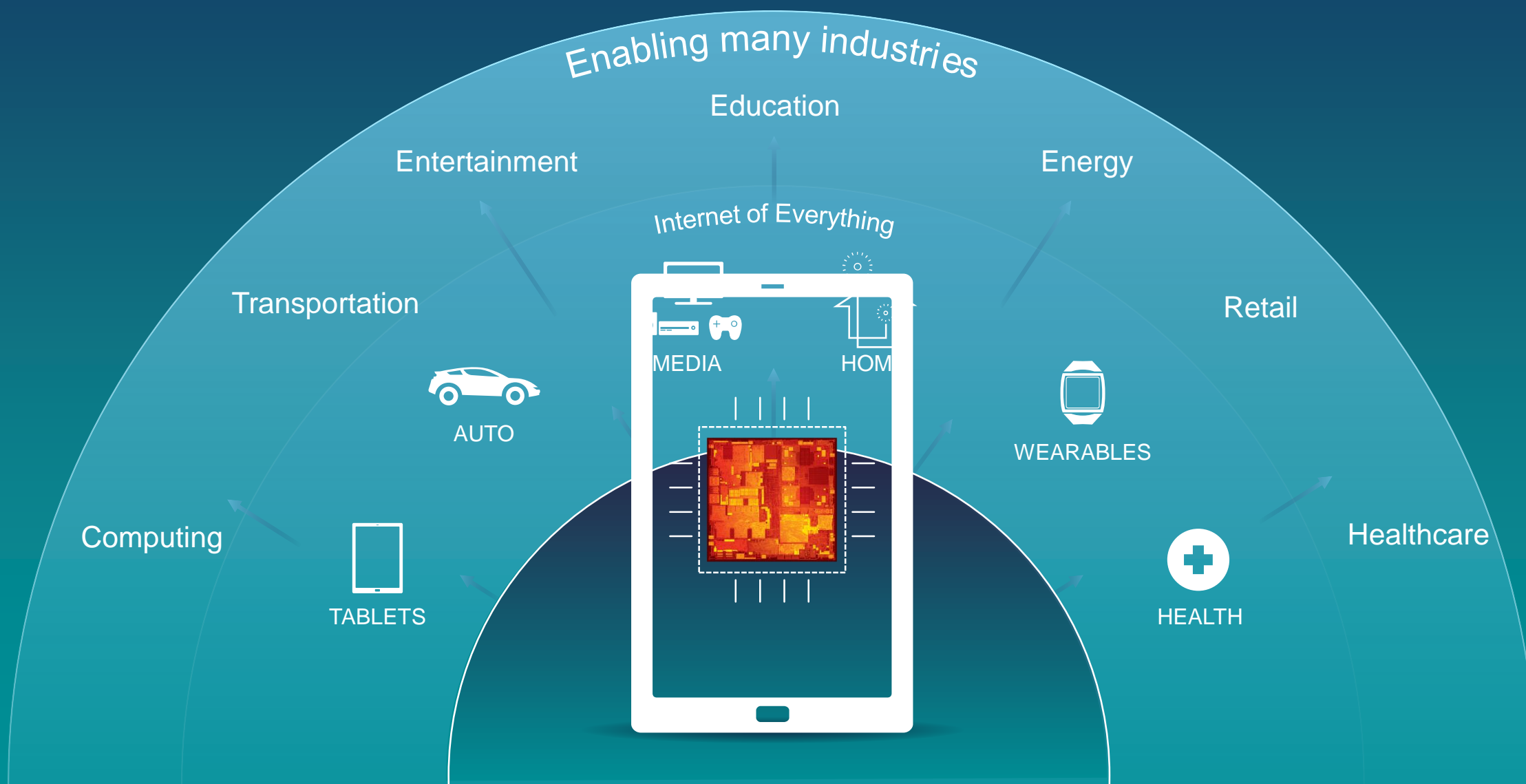
**~79%**

Watch video on their device

# Evolution of integrated sensors



# Expanding the mobile ecosystem beyond smartphones



# Moving Forward: Thinner, Lighter, Sleeker.



## Highly Integrated SoCs

Type 2: Perf + Multi-media + Connectivity

Type 1: Signal Processing + Connectivity

## Packaging Innovation

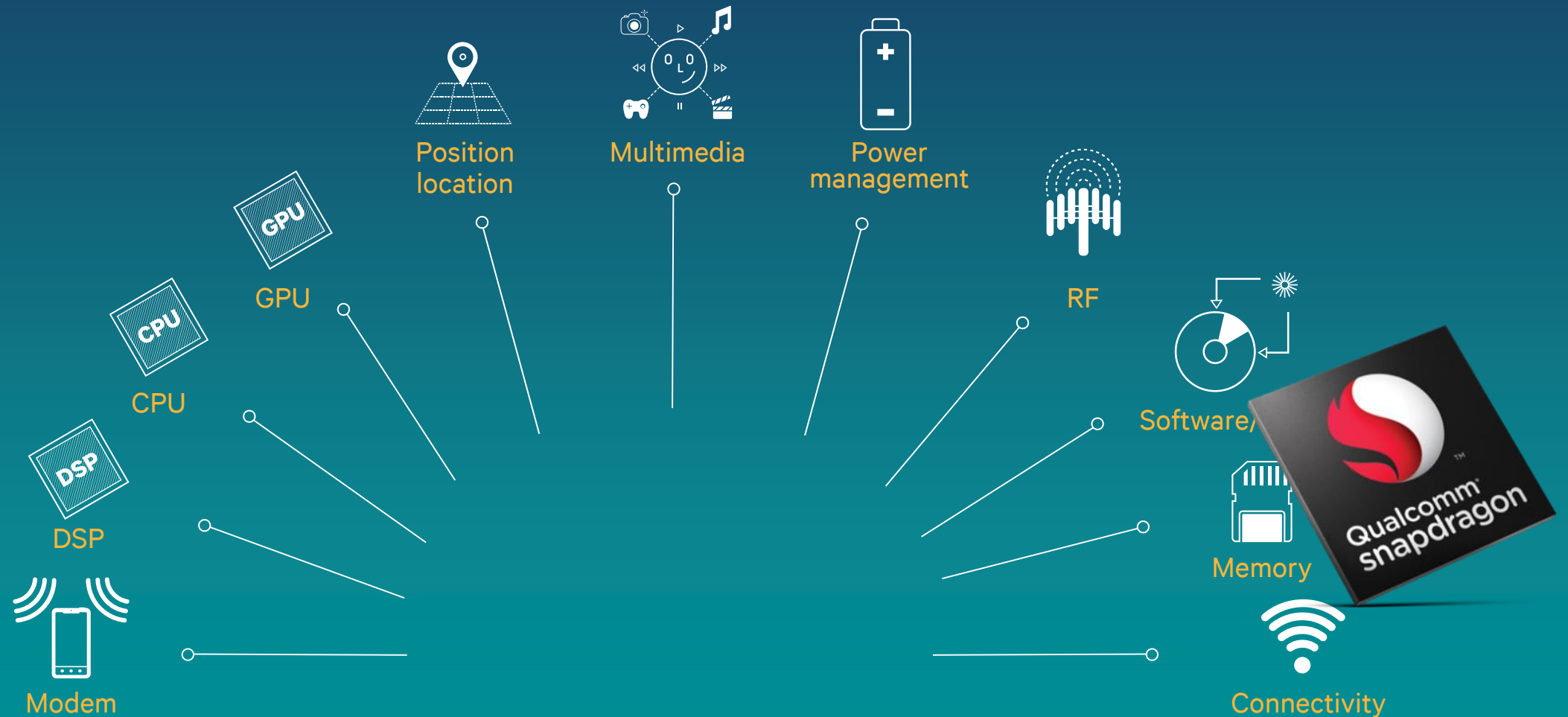
e.g. PoP packages

## Thermal Management

Friendly to body 24x7



# Integrated system solutions for automotive



# EVOLVING TRANSPORTATION

**~60% NEW CARS**  
shipped in 2017 will be connected through  
mobile technology





# TRANSFORMING HEALTH

**45% REDUCTION**  
in mortality rate for chronic disease  
patients using telehealth





# Connected Smarthome

>2X Connected Devices  
in the household from 2013 to 2020

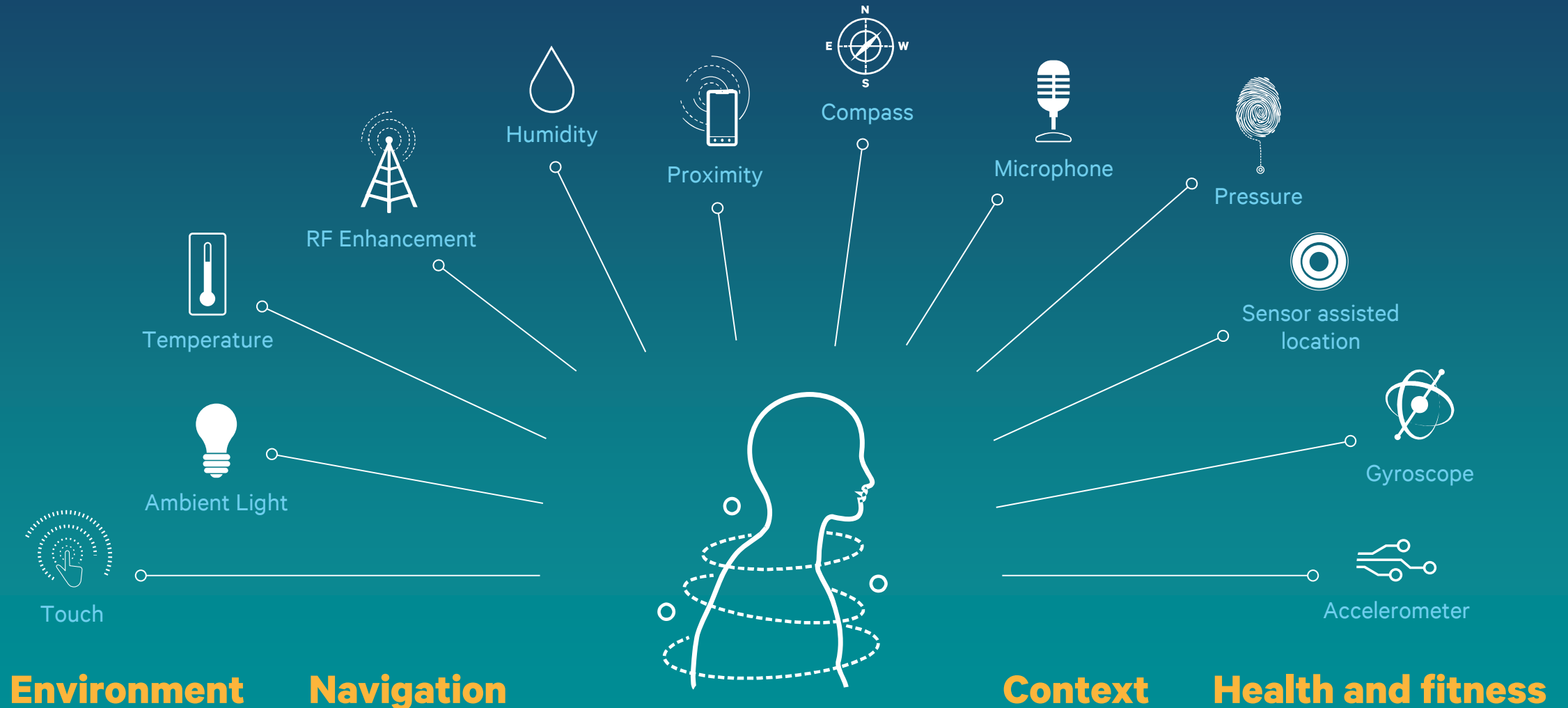
## ENABLING AWARENESS

Capturing data about you and  
your environment





# The future: Always **ON**. Always **SENSING**. Always **Connected**.



# Always on: 1 Day => 1 Week => 1 Month

## Power Challenge



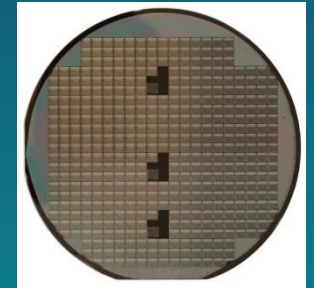
Low Power  
Architecture



Low Power  
Displays  
(e.g. Mirasol)



Aggressive  
Power Management



Low Power Process

# 2020 VISION



**>25 BILLION**  
connected devices by 2020



# 2020 VISION

- Always on
- Always connected
- Very low power
- Sensors everywhere
- Very hi degree of *cost-effective* integration

## *Technology Expectations*

- Continuation of Moore's Law
  - higher integration
  - lower power
  - lower cost
- Increasing "More than Moore"

## THE INTERNET OF EVERYTHING

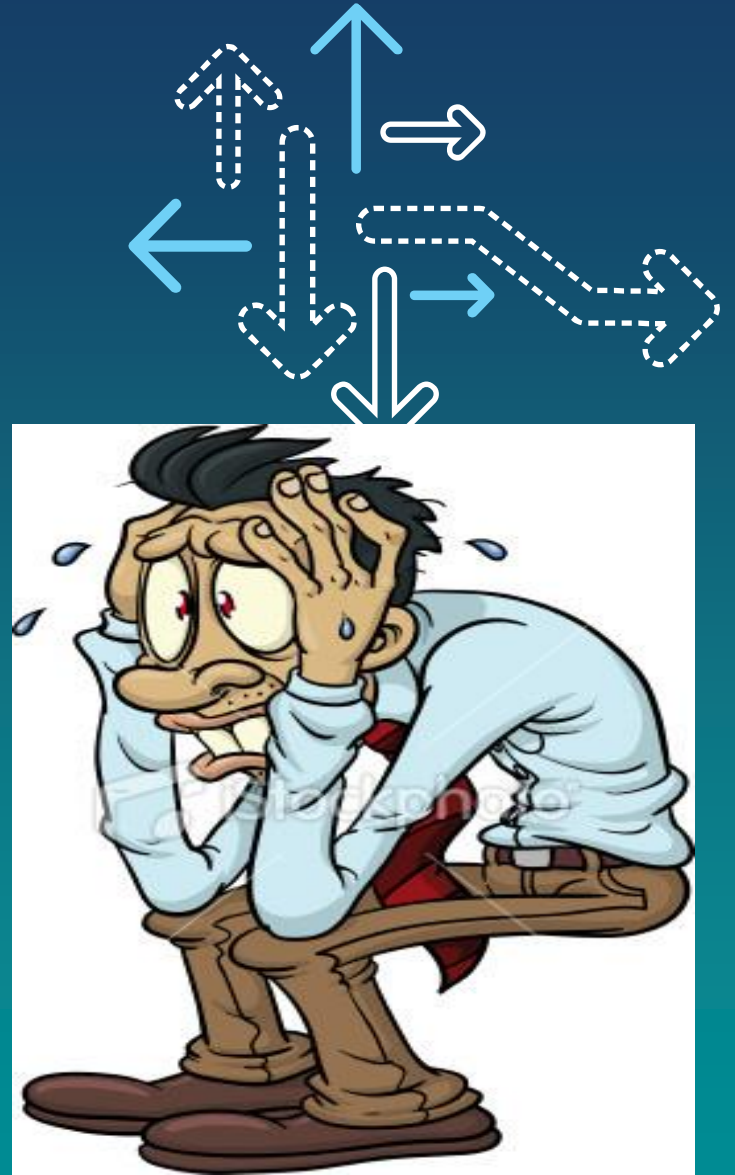


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# Continuing CMOS Scaling

## Die Cost Worries

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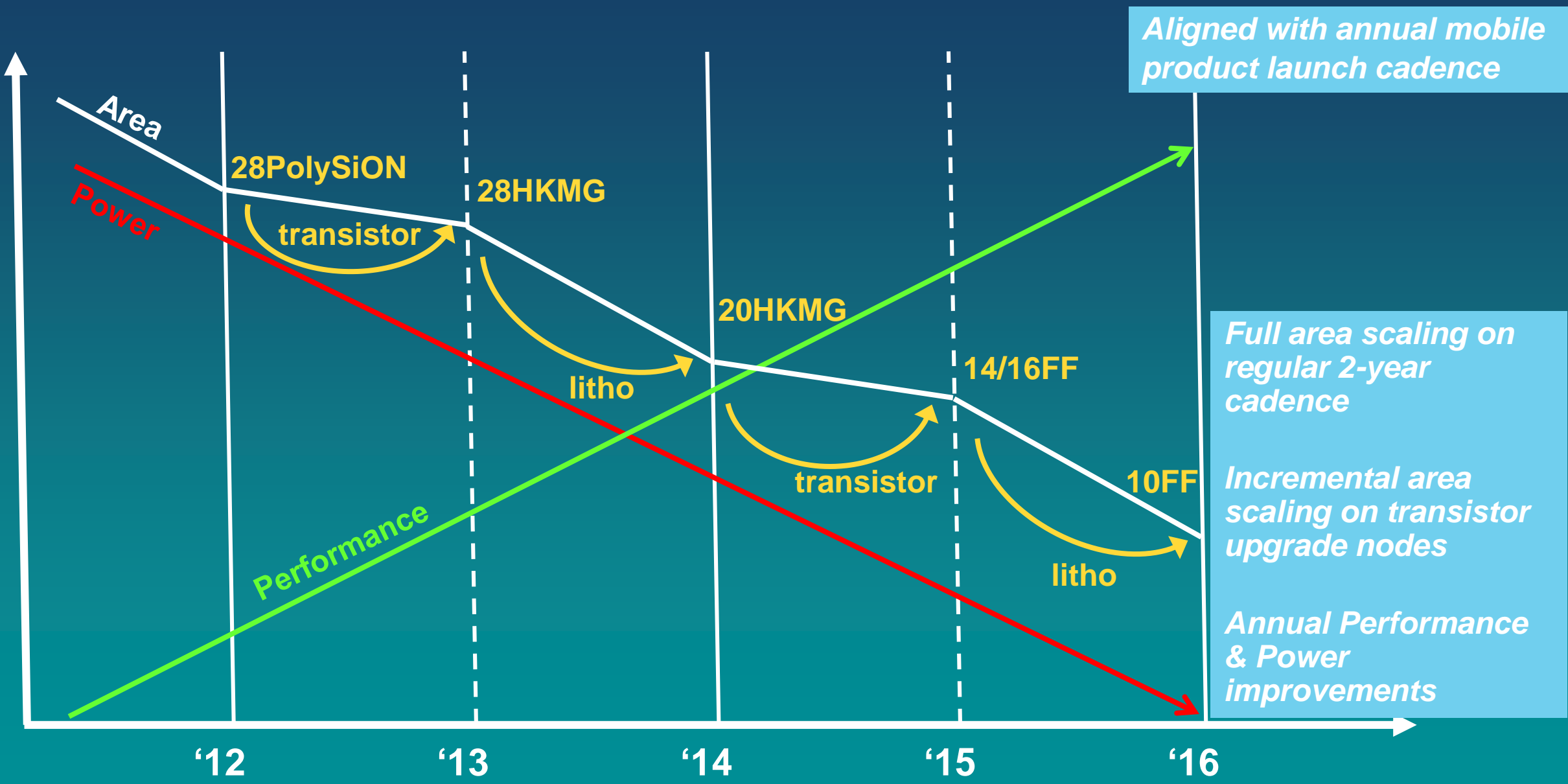
# Moore's Law

*...over the history of computing hardware, the number of transistors in a dense integrated circuit doubles approximately every two years*

- Gordon Moore, Intel co-founder, 1965

***Corollary: Economics dictate cost per transistor must also decrease!***

# Continuous innovation has provided annual technology cadence



# Diminishing CMOS Cost Improvement – Patterning Cost

Process complexity increasing by mask count increase

Aggressive pitch scaling to improve die cost by area scaling

Threat for putting more functionality in the same area



???

“traditional path”

- Primary culprit: litho cost

- New Materials Opportunities

- multi-pattern cost down

- EUV lithography

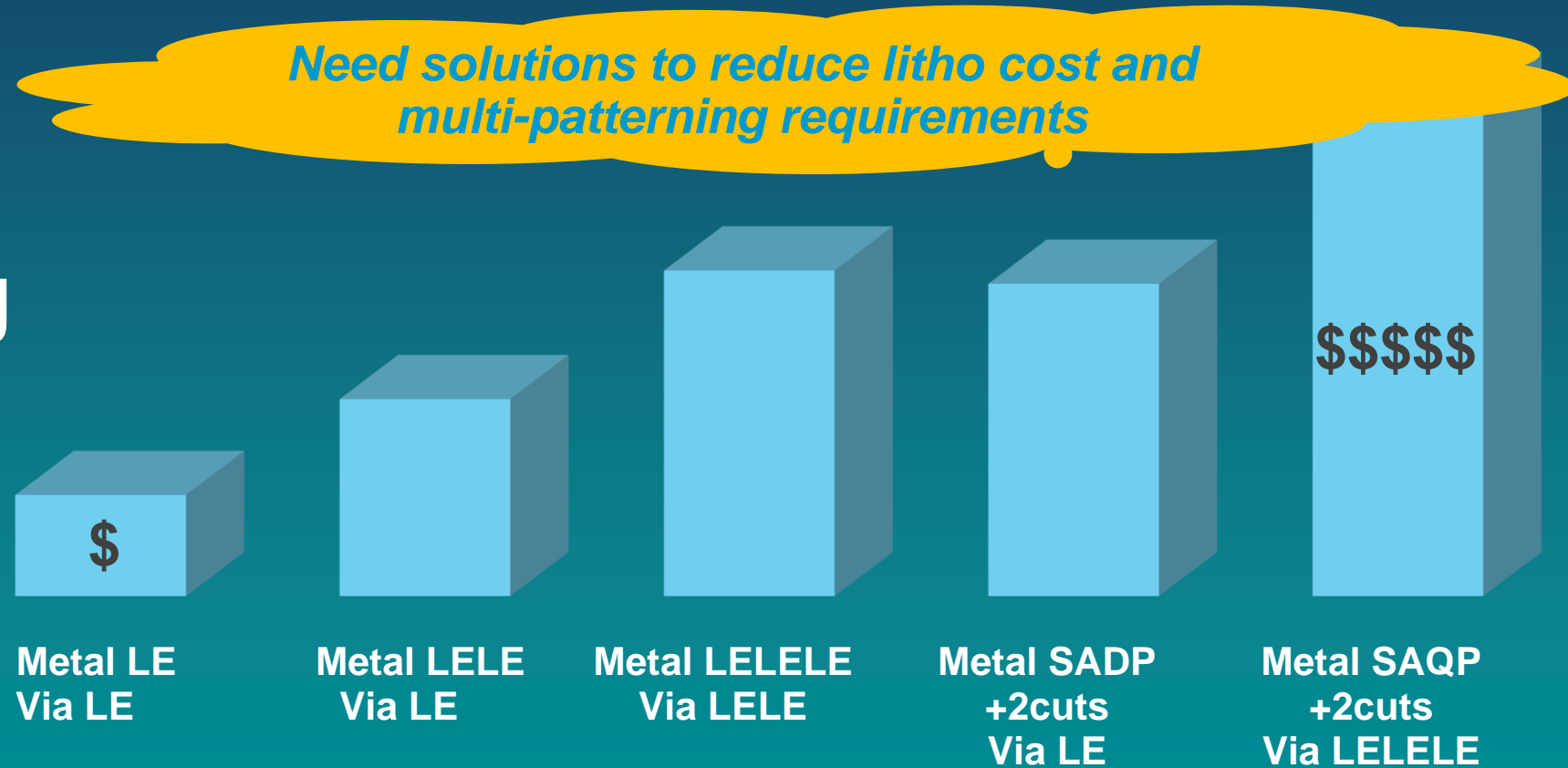
- Design/tech co-optimization

- ....



# 193i Multi-patterning cost explosion

## Patterning Cost



# Can we find a cost-effective litho solution for N7?

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***Need cost effective EUV AND 193i litho solution !***

# **EUV Potential Benefits in N7**

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## **Reduced wafer/die cost due to reduced mask count and better shrink**

- reducing MEOL complexity by 2D Metal1 intra-cell routing
- replacing repetitive depo & litho steps in 193i

## **Potential yield gains**

- reduced mask count
- reduced number of vias (DFM)

## **Potential area gains by less restrictions in layout**

# EUV/N7 Timing

When is decision point for N7?

AT MOST within one year from now (Q4'15)



Need to demonstrate readiness of EUV in all aspects (source, resist, mask, etc.) in order to irreversibly integrate into N7 flows

Demonstrate in a “reversible” manufacturing environment (14nm/10nm?) as an option



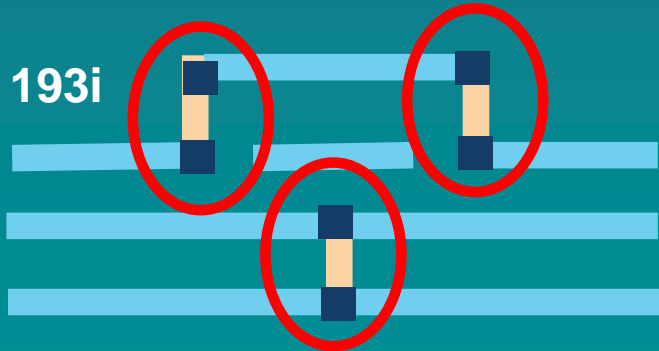
# 2D EUV layout benefits

Able to employ jogs

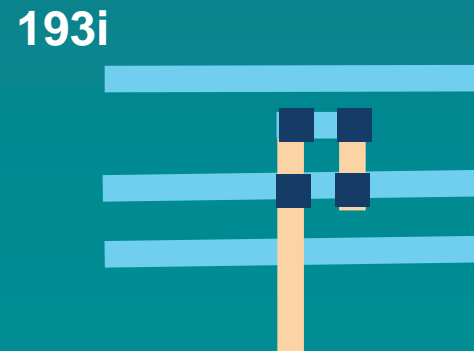
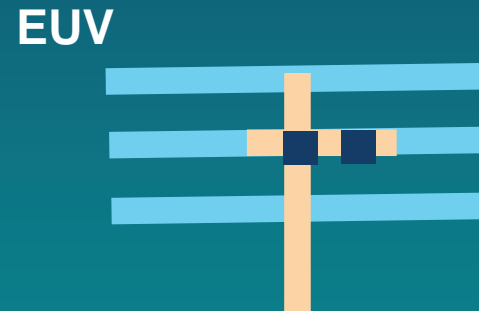
Reduced #vias (better yield)

Less min length (area) wires

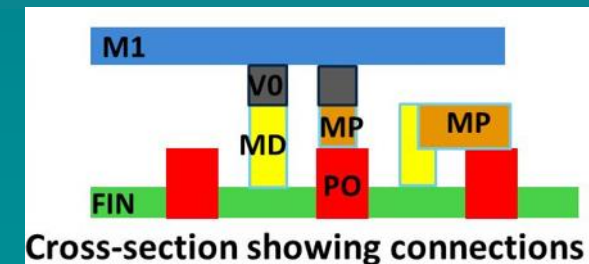
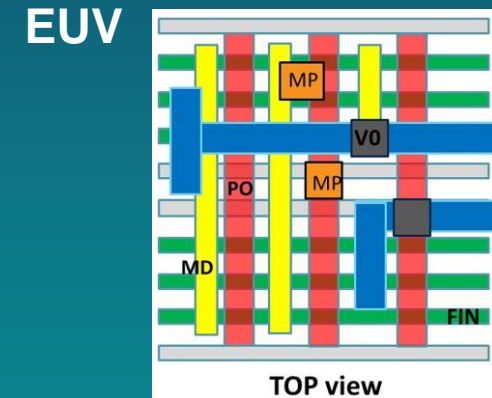
Able to connect to neighbor wire



**Better freedom for  
redundant via  
insertion**

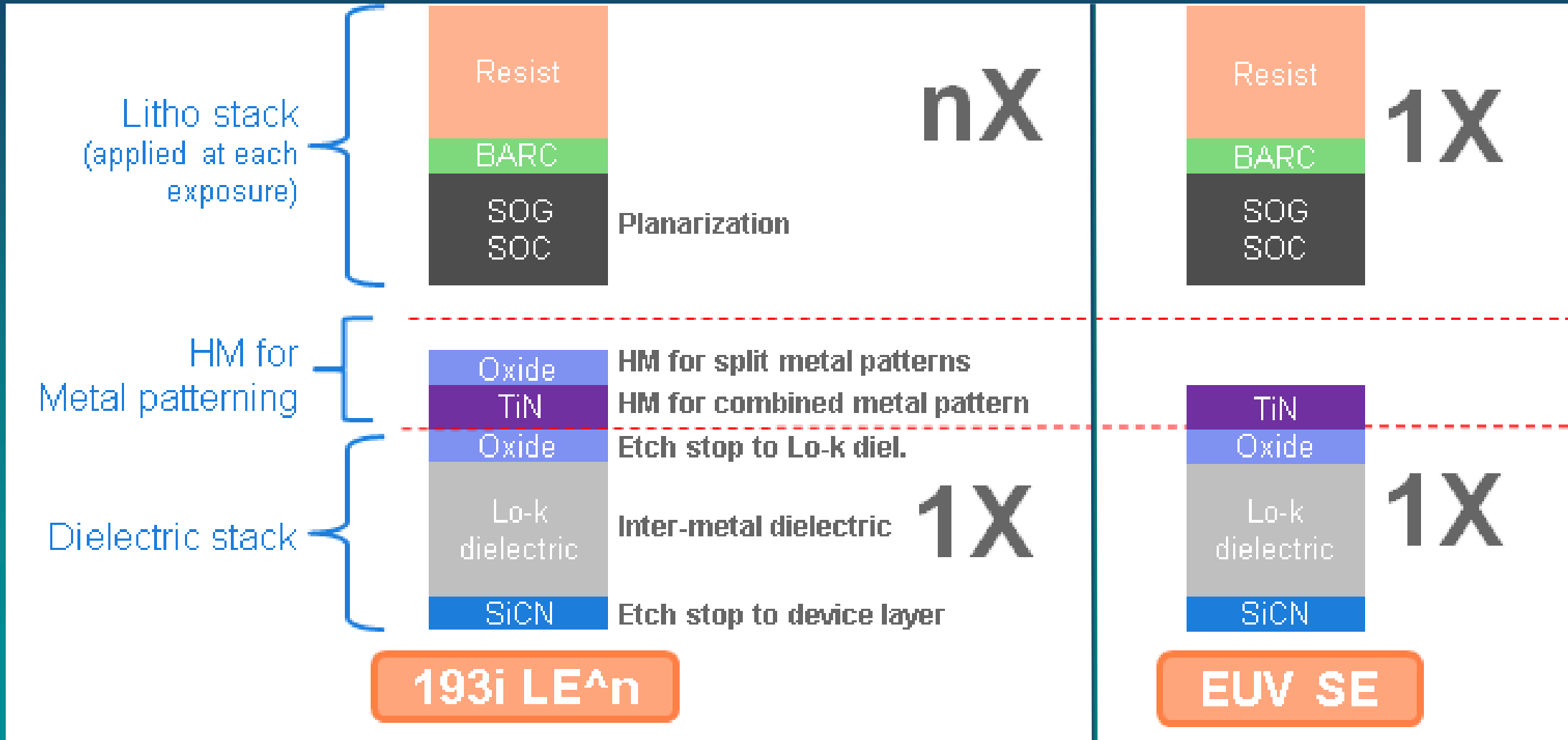


**Reduced MOL  
complexity  
by 2D M1**

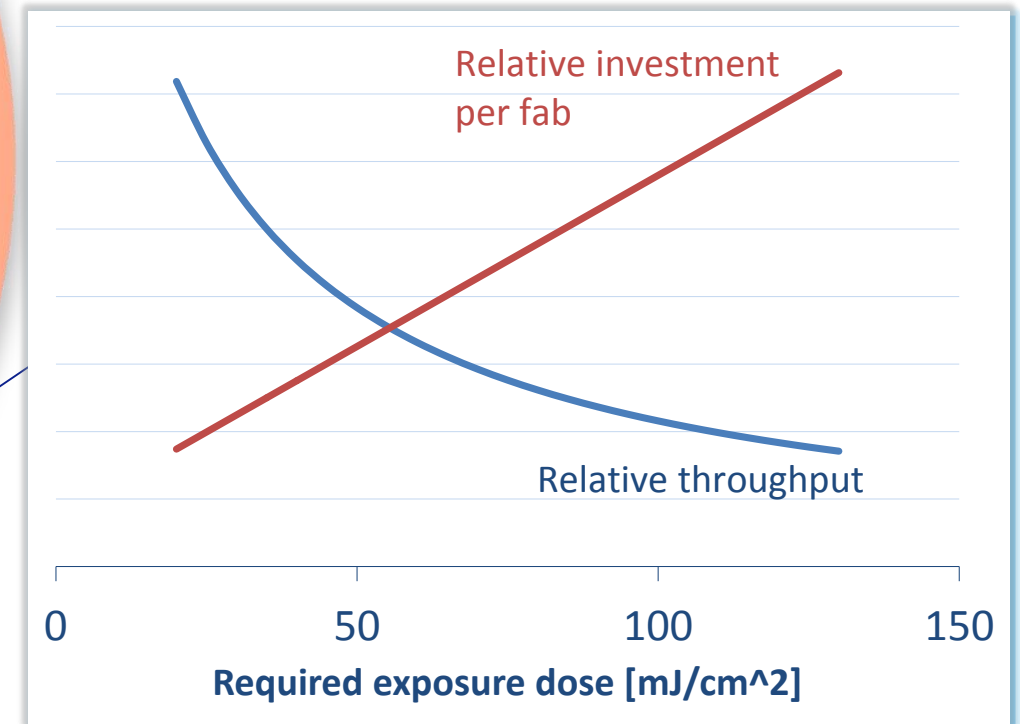
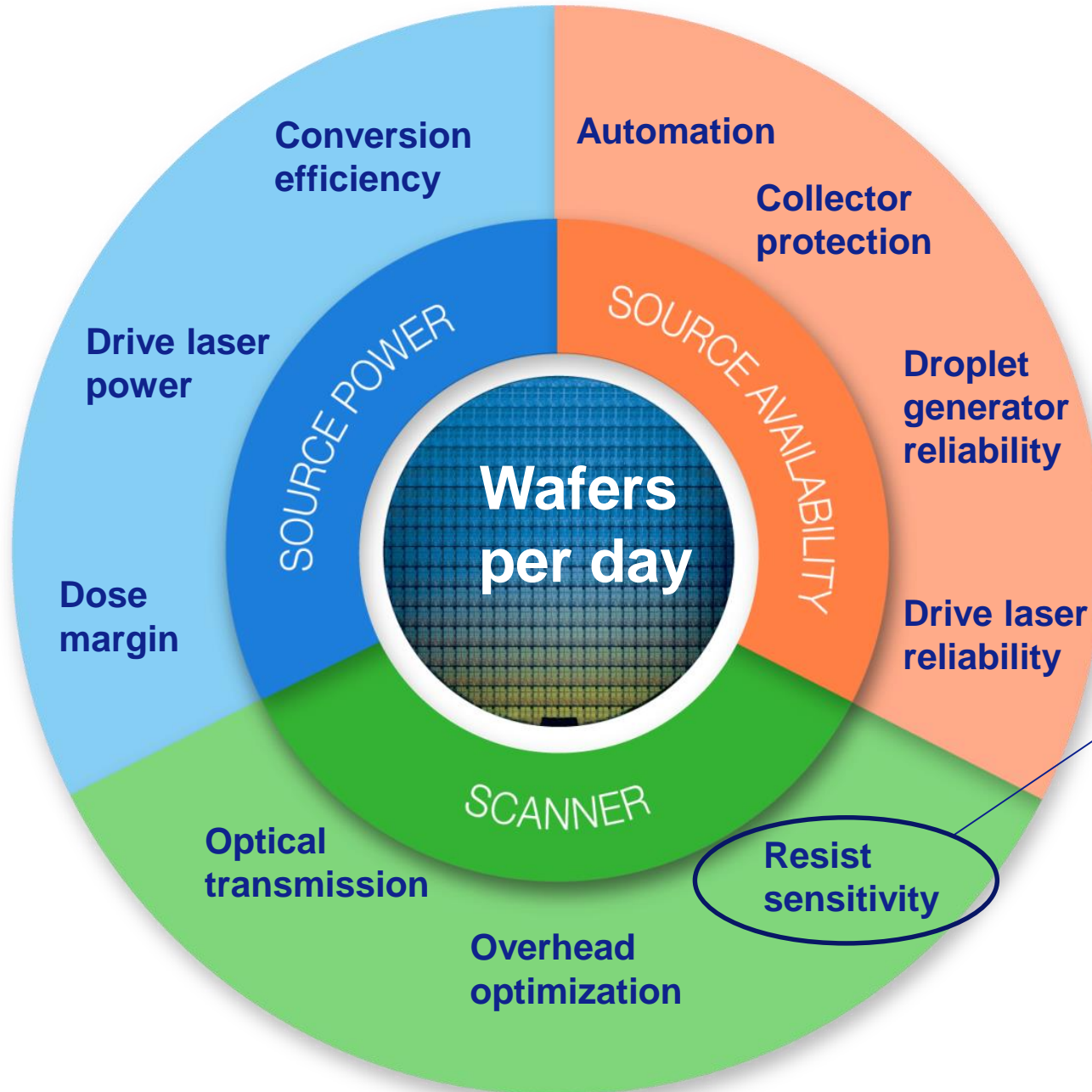


# Number of deposition, litho, and etch steps reduced with EUV

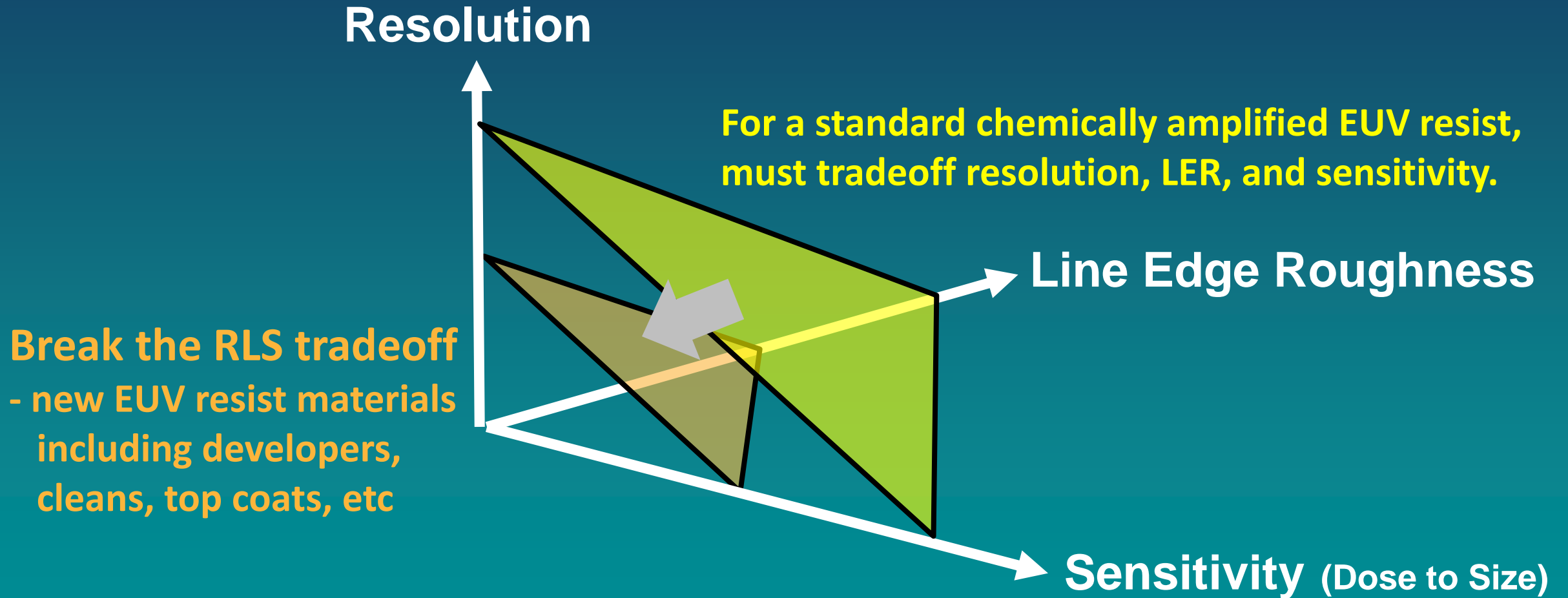
## Metal patterning



# EUV productivity is determined by a number of factors



# Need for highly-sensitive EUV resists for increased productivity while meeting resolution and LER requirements



# Summary

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Mobile revolution will continue to rely on Moore's Law to deliver increased integration, power reduction and value to consumers

Patterning costs are exploding and may limit expected cost reduction in the future – innovation is needed

- 193i multi-patterning cost reduction, EUV, DSA, etc.

N10 will not use EUV lithography. EUV is a candidate for N7 to reduce patterning cost

- Full feasibility for practical manufacturability must to be demonstrated by Q4'15 for irreversible commitment to EUV in N7

- Need to demonstrate EUV as an optional step in existing manufacturing environment with 193i as backup (14nm/10nm?)



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# Thank you!

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